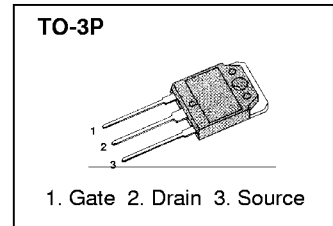


**FEATURES**

- Advanced New Design
- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Very Low Intrinsic Capacitances
- Excellent Switching Characteristics
- Unrivalled Gate Charge: 70nC (Typ.)
- Extended Safe Operating Area
- Lower  $R_{DS(ON)}$ : 0.43Ω (Typ.)

$BV_{DSS} = 700V$   
 $R_{DS(ON)} = 0.56\Omega$   
 $I_D = 15A$



**ABSOLUTE MAXIMUM RATINGS**

Symbol	Characteristics	Value	Units
$V_{DSS}$	Drain-to-Source Voltage	700	V
$I_D$	Continuous Drain Current ( $T_C = 25^\circ C$ )	15	A
	Continuous Drain Current ( $T_C = 100^\circ C$ )	9.5	
$I_{DM}$	Drain Current-Pulsed ①	60	A
$V_{GS}$	Gate-to-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy ②	950	mJ
$I_{AR}$	Avalanche Current ①	15	A
$E_{AR}$	Repetitive Avalanche Energy ①	30	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.5	V/ns
$P_D$	Total Power Dissipation ( $T_C = 25^\circ C$ )	300	W W/°C
	Linear Derating Factor	2.38	
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +150	°C
$T_L$	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

**THERMAL RESISTANCE**

Symbol	Characteristics	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	-	0.42	°C/W
$R_{\theta CS}$	Case-to-Sink	0.24	-	
$R_{\theta JA}$	Junction-to-Ambient	-	40	

**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Characteristics	Min.	Typ.	Max.	Units	Test Conditions
$BV_{DSS}$	Drain-Source Breakdown Voltage	700	–	–	V	$V_{GS}=0\text{V}$ , $I_D=250\mu\text{A}$
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	–	0.68	–	V/ $^\circ\text{C}$	$I_D=250\mu\text{A}$ , <b>See Fig 7</b>
$V_{GS(th)}$	Gate Threshold Voltage	3.0	–	5.0	V	$V_{DS}=5\text{V}$ , $I_D=250\mu\text{A}$
$I_{GSS}$	Gate-Source Leakage, Forward	–	–	100	nA	$V_{GS}=30\text{V}$
	Gate-Source Leakage, Reverse	–	–	–100		$V_{GS}= -30\text{V}$
$I_{DSS}$	Drain-to-Source Leakage Current	–	–	10	$\mu\text{A}$	$V_{DS}=700\text{V}$
		–	–	100		$V_{DS}=560\text{V}$ , $T_C=125^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-State Resistance	–	0.43	0.56	$\Omega$	$V_{GS}=10\text{V}$ , $I_D=7.5\text{A}$ ④
$g_{fs}$	Forward Transconductance	–	15	–	S	$V_{DS}=50\text{V}$ , $I_D=7.5\text{A}$ ④
$C_{iss}$	Input Capacitance	–	2790	3630	pF	$V_{GS}=0\text{V}$ , $V_{DS}=25\text{V}$ $f=1\text{MHz}$ <b>See Fig 5</b>
$C_{oss}$	Output Capacitance	–	300	390		
$C_{rss}$	Reverse Transfer Capacitance	–	27	35		
$t_{d(on)}$	Turn-On Delay Time	–	70	150	ns	$V_{DD}=350\text{V}$ , $I_D=15\text{A}$ $R_G=50\Omega$ <b>See Fig 13</b> ④ ⑤
$t_r$	Rise Time	–	180	370		
$t_{d(off)}$	Turn-Off Delay Time	–	160	330		
$t_f$	Fall Time	–	120	250		
$Q_g$	Total Gate Charge	–	70	90	nC	$V_{DS}=560\text{V}$ , $V_{GS}=10\text{V}$ $I_D=15\text{A}$ <b>See Fig 6 &amp; Fig 12</b> ④ ⑤
$Q_{gs}$	Gate-Source Charge	–	17	–		
$Q_{gd}$	Gate-Drain (Miller) Charge	–	33	–		

**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS**

Symbol	Characteristics	Min.	Typ.	Max.	Units	Test Conditions
$I_S$	Continuous Source Current	–	–	15	A	Integral reverse pn-diode in the MOSFET
$I_{SM}$	Pulsed-Source Current ①	–	–	60		
$V_{SD}$	Diode Forward Voltage ④	–	–	1.4	V	$T_J=25^\circ\text{C}$ , $I_S=15\text{A}$ , $V_{GS}=0\text{V}$
$t_{rr}$	Reverse Recovery Time	–	460	–	ns	$T_J=25^\circ\text{C}$ , $I_F=15\text{A}$ , $V_{DD}=560\text{V}$ $di_F/dt=100\text{A}/\mu\text{s}$ ④
$Q_{rr}$	Reverse Recovery Charge	–	5.7	–	$\mu\text{C}$	

**Notes:**

- ① Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
- ②  $L=7.8\text{mH}$ ,  $I_{AS}=15\text{A}$ ,  $V_{DD}=50\text{V}$ ,  $R_G=25\Omega$ , Starting  $T_J=25^\circ\text{C}$
- ③  $I_{SD} \leq 15\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J=25^\circ\text{C}$
- ④ Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$
- ⑤ Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

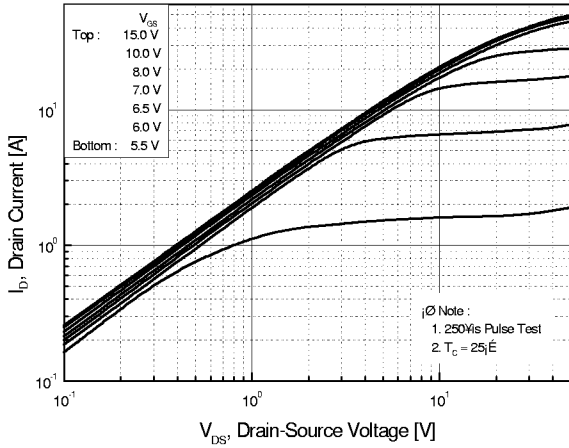


Fig 2. Transfer Characteristics

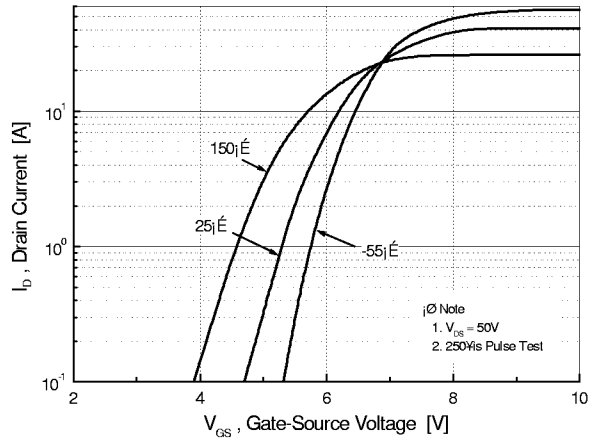


Fig 3. On-Resistance vs. Drain Current

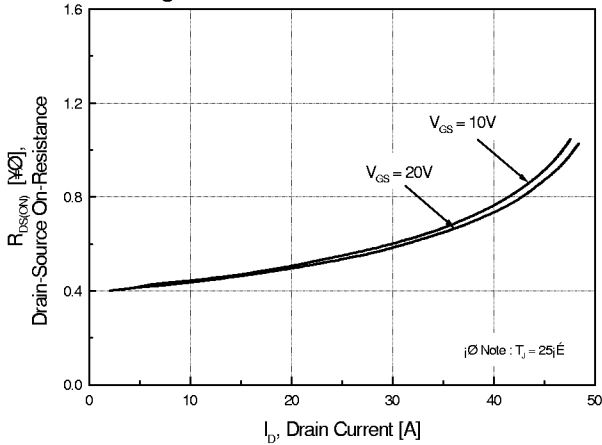


Fig 4. Source-Drain Diode Forward Voltage

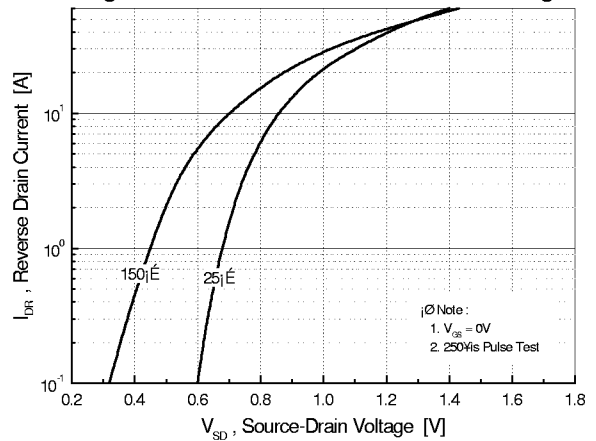


Fig 5. Capacitance vs. Drain-Source Voltage

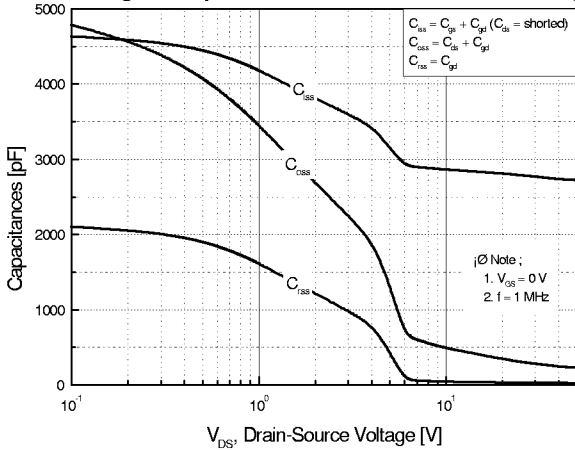


Fig 6. Gate Charge vs. Gate-Source Voltage

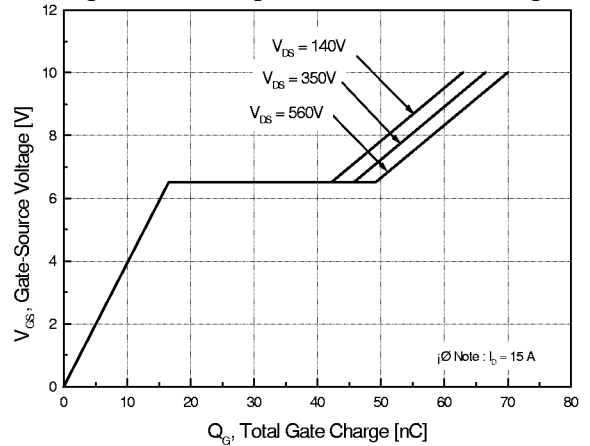


Fig 7. Breakdown Voltage vs. Temperature

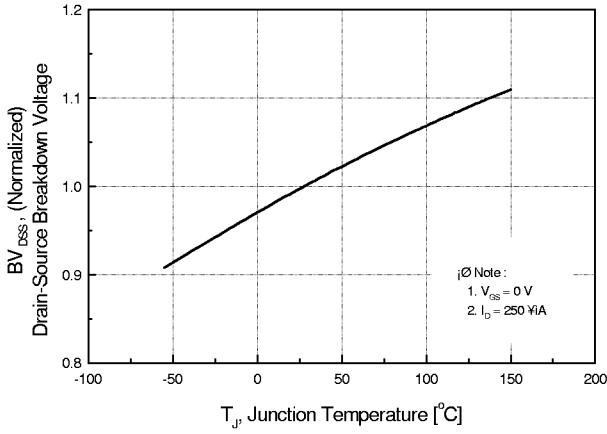


Fig 8. On-Resistance vs. Temperature

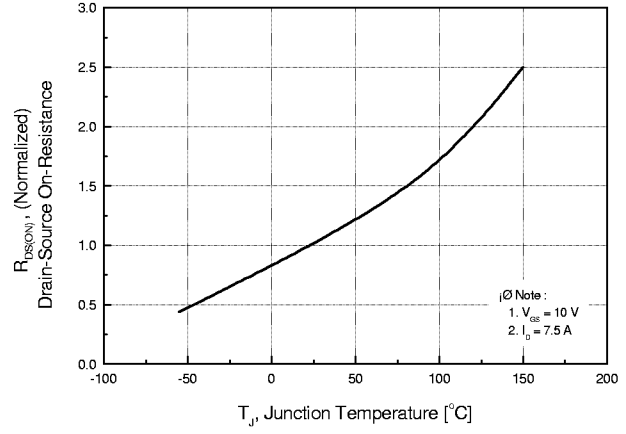


Fig 9. Max. Safe Operating Area

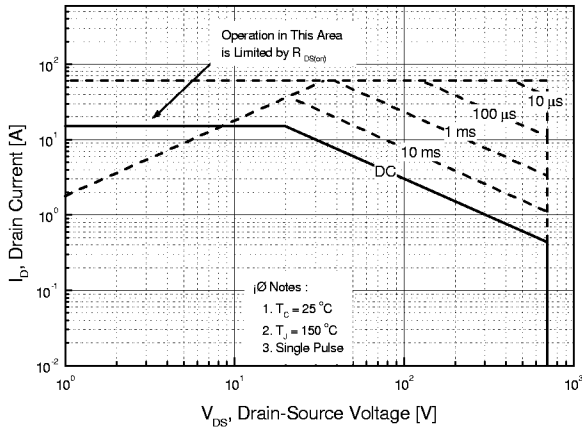


Fig 10. Max. Drain Current vs. Case Temperature

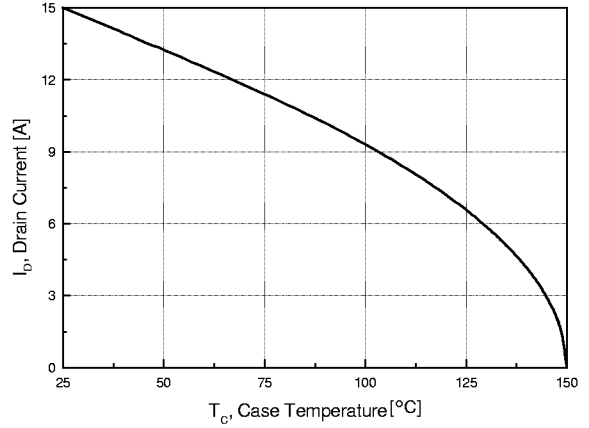


Fig 11. Thermal Response

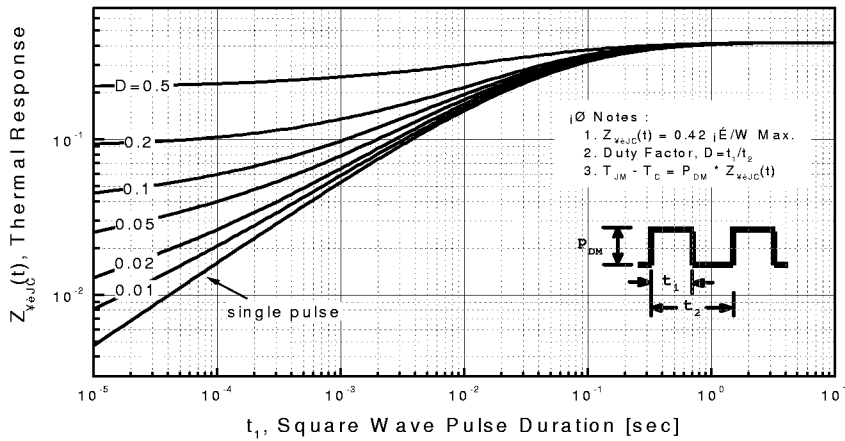


Fig 12. Gate Charge Test Circuit & Waveform

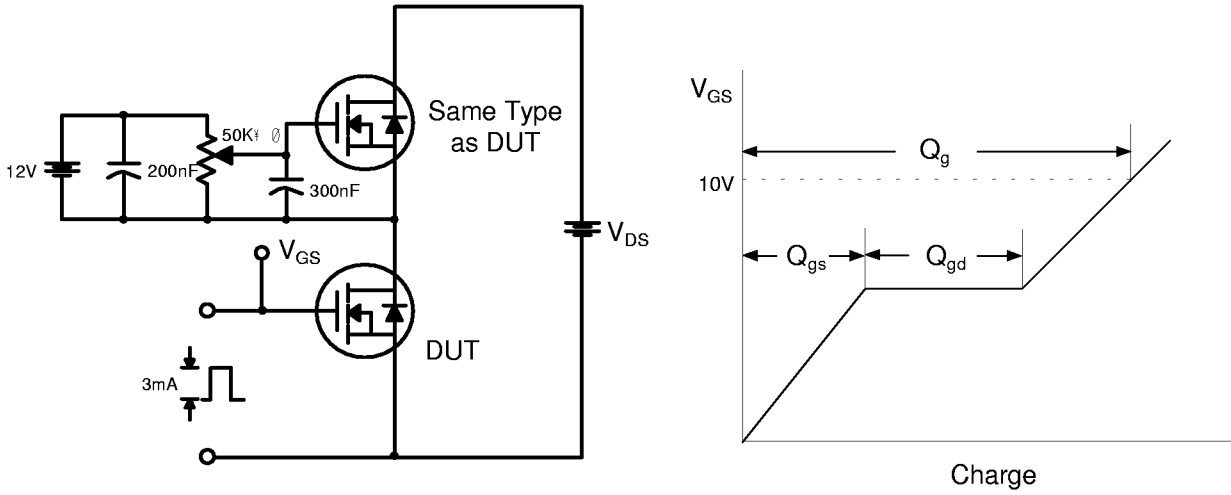


Fig 13. Resistive Switching Test Circuit & Waveforms

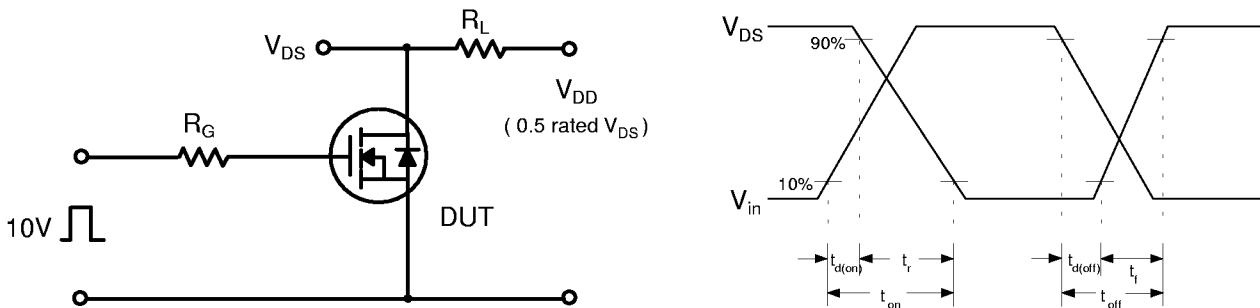


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

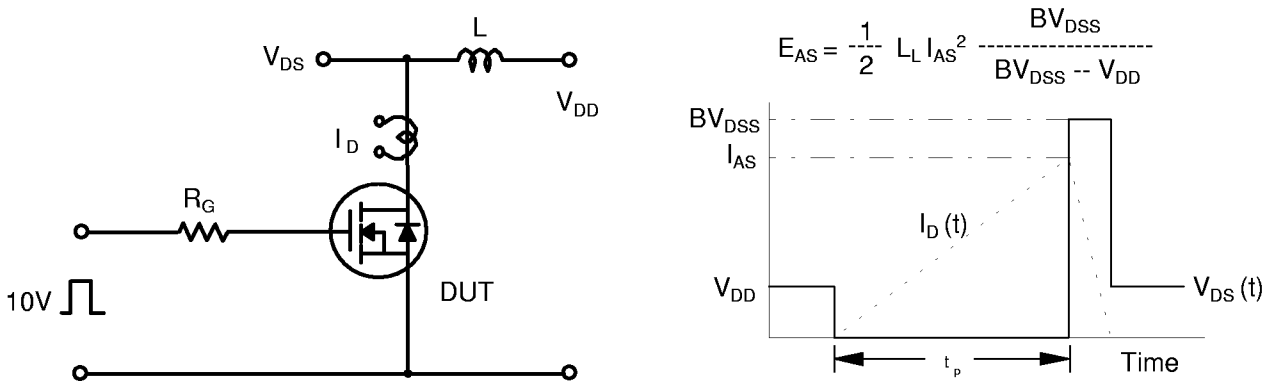
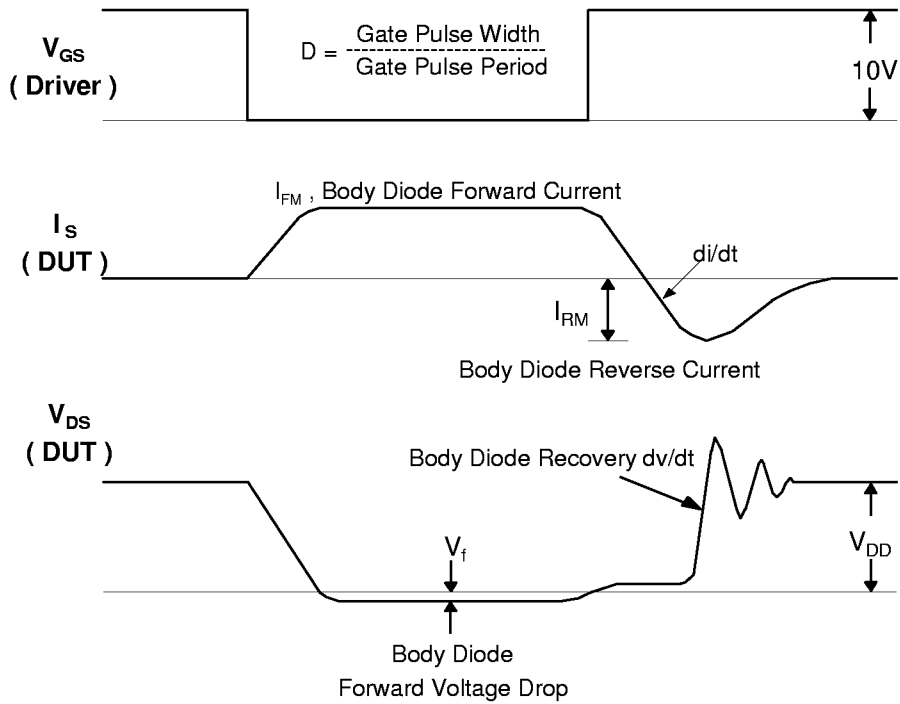
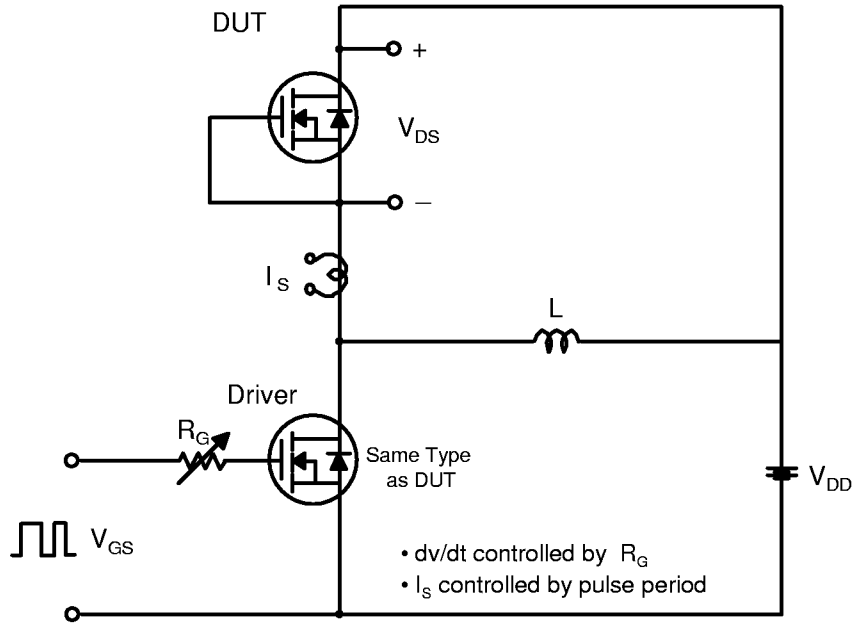
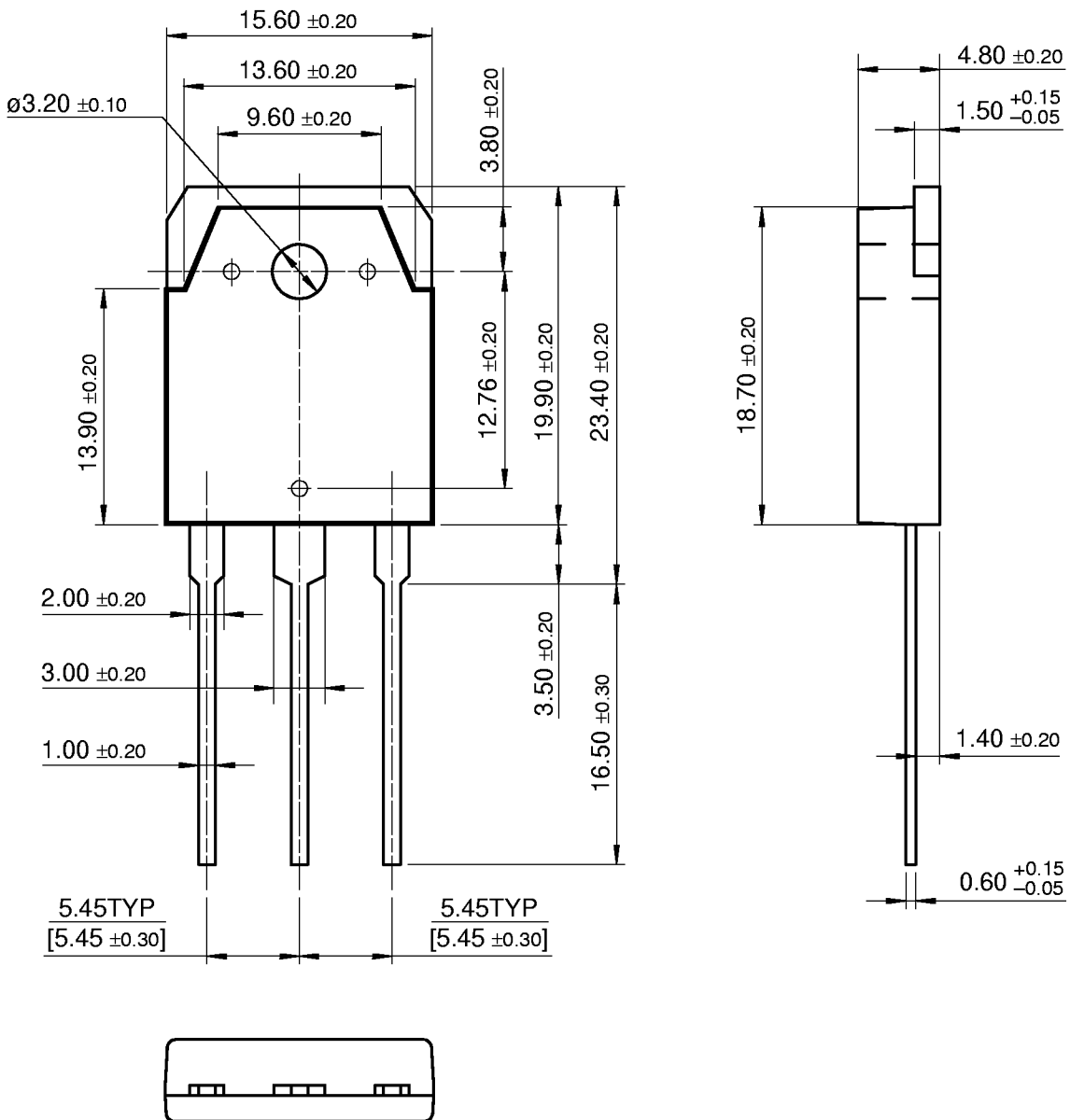


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



TO-3P Package Dimensions

TO-3P (FS PKG CODE AF)



Dimensions in Millimeters  
September 1999, Rev B